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# FQA13N50C\_F109

## N-Channel QFET® MOSFET

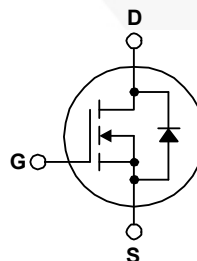
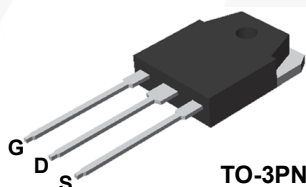
500 V, 13.5 A, 480 mΩ

### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

### Features

- 13.5 A, 500 V,  $R_{DS(on)} = 480 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 6.75 \text{ A}$
- Low Gate Charge (Typ. 43 nC)
- Low  $C_{rss}$  (Typ. 20 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability



### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted.

| Symbol         | Parameter                                                             | FQA13N50C_F109 | Unit                |
|----------------|-----------------------------------------------------------------------|----------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage                                                  | 500            | V                   |
| $I_D$          | Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )               | 13.5           | A                   |
|                | - Continuous ( $T_C = 100^\circ\text{C}$ )                            | 8.5            | A                   |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)                                       | 54             | A                   |
| $V_{GSS}$      | Gate-Source Voltage                                                   | $\pm 30$       | V                   |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                               | 860            | mJ                  |
| $I_{AR}$       | Avalanche Current (Note 1)                                            | 13.5           | A                   |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                  | 21.8           | mJ                  |
| dv/dt          | Peak Diode Recovery dv/dt (Note 3)                                    | 4.5            | V/ns                |
| $P_D$          | Power Dissipation ( $T_C = 25^\circ\text{C}$ )                        | 218            | W                   |
|                | - Derate above $25^\circ\text{C}$                                     | 1.56           | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                               | -55 to +150    | $^\circ\text{C}$    |
| $T_L$          | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds. | 300            | $^\circ\text{C}$    |

### Thermal Characteristics

| Symbol          | Parameter                                     | FQA13N50C_F109 | Unit               |
|-----------------|-----------------------------------------------|----------------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max.    | 0.58           | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 40             | $^\circ\text{C/W}$ |

## Package Marking and Ordering Information

| Part Number    | Top Mark  | Package | Packing Method | Reel Size | Tape Width | Quantity |
|----------------|-----------|---------|----------------|-----------|------------|----------|
| FQA13N50C_F109 | FQA13N50C | TO-3PN  | Tube           | N/A       | N/A        | 30 units |

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

### Off Characteristics

|                                |                                           |                                                                   |     |     |      |                    |
|--------------------------------|-------------------------------------------|-------------------------------------------------------------------|-----|-----|------|--------------------|
| $BV_{DSS}$                     | Drain-Source Breakdown Voltage            | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$               | 500 | --  | --   | V                  |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$ | --  | 0.5 | --   | $V/^\circ\text{C}$ |
| $I_{DSS}$                      | Zero Gate Voltage Drain Current           | $V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$                      | --  | --  | 1    | $\mu\text{A}$      |
|                                |                                           | $V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$                  | --  | --  | 10   | $\mu\text{A}$      |
| $I_{GSSF}$                     | Gate-Body Leakage Current, Forward        | $V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$                       | --  | --  | 100  | nA                 |
| $I_{GSSR}$                     | Gate-Body Leakage Current, Reverse        | $V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$                      | --  | --  | -100 | nA                 |

### On Characteristics

|              |                                   |                                                 |     |      |      |          |
|--------------|-----------------------------------|-------------------------------------------------|-----|------|------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2.0 | --   | 4.0  | V        |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10\text{ V}, I_D = 6.75\text{ A}$     | --  | 0.39 | 0.48 | $\Omega$ |
| $g_{FS}$     | Forward Transconductance          | $V_{DS} = 40\text{ V}, I_D = 6.75\text{ A}$     | --  | 15   | --   | S        |

### Dynamic Characteristics

|           |                              |                                                                      |    |      |      |    |
|-----------|------------------------------|----------------------------------------------------------------------|----|------|------|----|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1.0\text{ MHz}$ | -- | 1580 | 2055 | pF |
| $C_{oss}$ | Output Capacitance           |                                                                      | -- | 180  | 235  | pF |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                      | -- | 20   | 25   | pF |

### Switching Characteristics

|              |                     |                                                                           |    |      |     |    |
|--------------|---------------------|---------------------------------------------------------------------------|----|------|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = 250\text{ V}, I_D = 13.5\text{ A},$<br>$R_G = 25\text{ }\Omega$ | -- | 25   | 60  | ns |
| $t_r$        | Turn-On Rise Time   |                                                                           | -- | 100  | 210 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time |                                                                           | -- | 130  | 270 | ns |
| $t_f$        | Turn-Off Fall Time  | (Note 4)                                                                  | -- | 100  | 210 | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = 400\text{ V}, I_D = 13.5\text{ A},$<br>$V_{GS} = 10\text{ V}$   | -- | 43   | 56  | nC |
| $Q_{gs}$     | Gate-Source Charge  |                                                                           | -- | 7.5  | --  | nC |
| $Q_{gd}$     | Gate-Drain Charge   | (Note 4)                                                                  | -- | 18.5 | --  | nC |

### Drain-Source Diode Characteristics and Maximum Ratings

|                 |                                                       |                                                                                    |    |     |     |    |
|-----------------|-------------------------------------------------------|------------------------------------------------------------------------------------|----|-----|-----|----|
| I <sub>S</sub>  | Maximum Continuous Drain-Source Diode Forward Current |                                                                                    | -- | --  | 13  | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain-Source Diode Forward Current     |                                                                                    | -- | --  | 52  | A  |
| V <sub>SD</sub> | Drain-Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 13.5 A                                     | -- | --  | 1.4 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                 | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 13.5 A,<br>dI <sub>F</sub> / dt = 100 A/μs | -- | 410 | --  | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                               |                                                                                    | -- | 4.5 | --  | μC |

#### Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2.  $L = 5.6\text{ mH}$ ,  $I_{AS} = 13.5\text{ A}$ ,  $V_{DD} = 50\text{ V}$ ,  $R_G = 25\text{ }\Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 13.5\text{ A}$ ,  $dI/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature

## Typical Characteristics

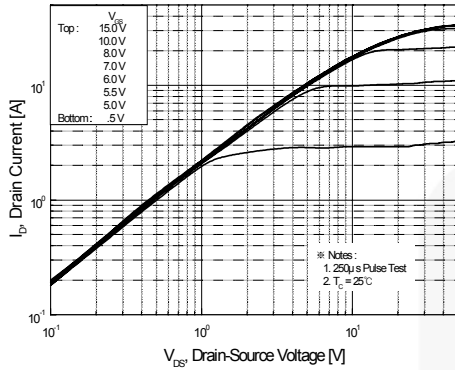


Figure 1. On-Region Characteristics

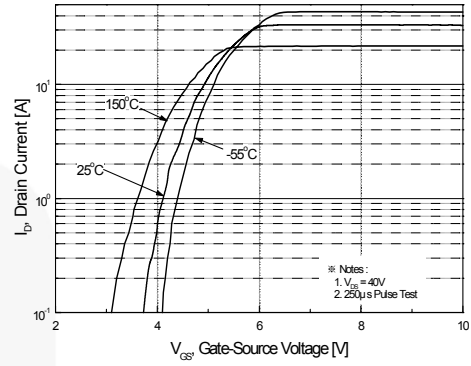


Figure 2. Transfer Characteristics

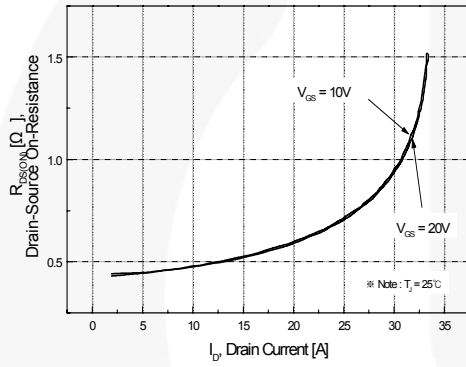


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

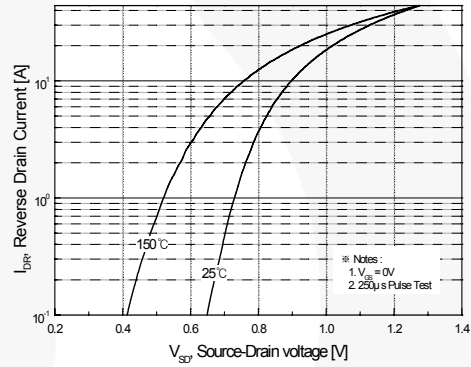


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

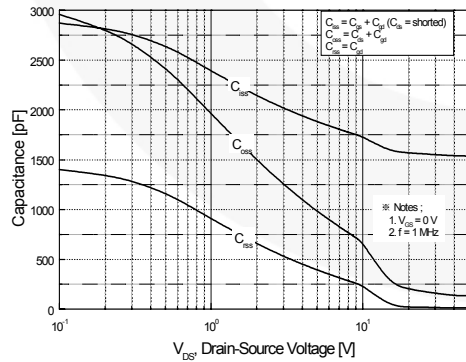


Figure 5. Capacitance Characteristics

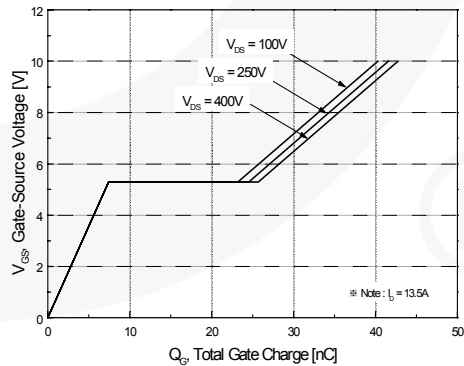


Figure 6. Gate Charge Characteristics

## Typical Characteristics (Continued)

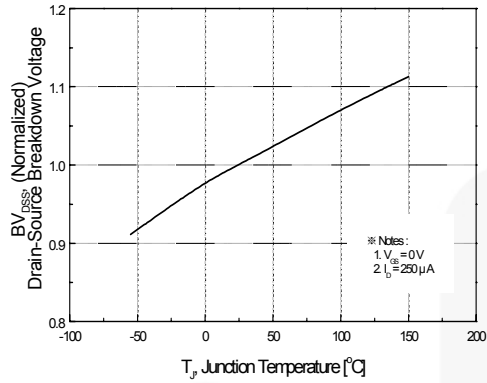


Figure 7. Breakdown Voltage Variation vs Temperature

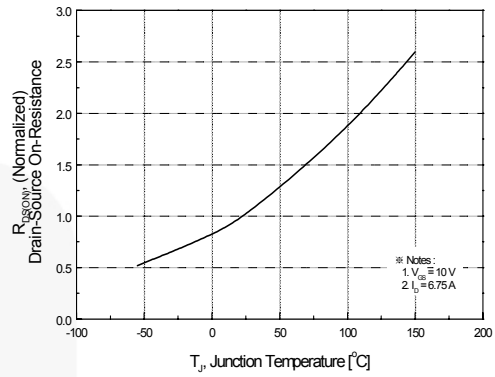


Figure 8. On-Resistance Variation vs Temperature

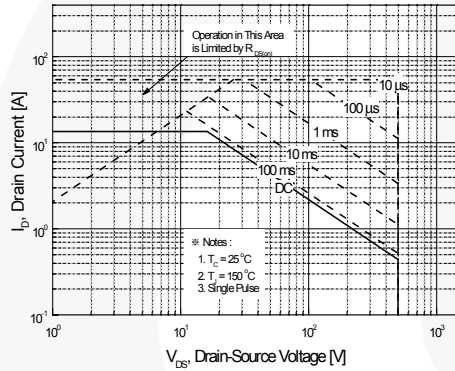


Figure 9. Maximum Safe Operating Area

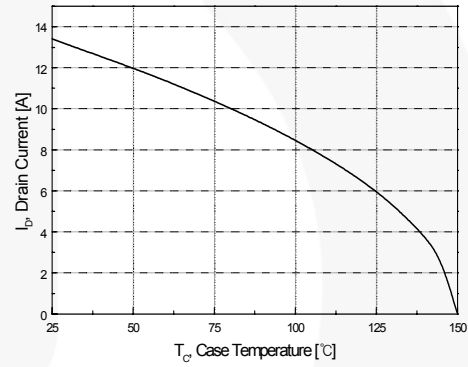


Figure 10. Maximum Drain Current vs Case Temperature

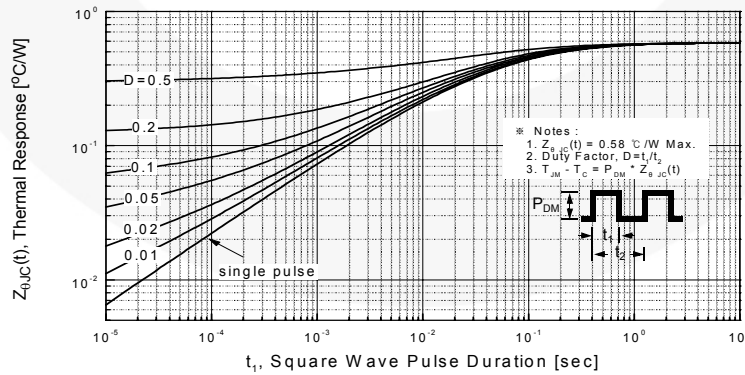


Figure 11. Transient Thermal Response Curve for FQA13N50C

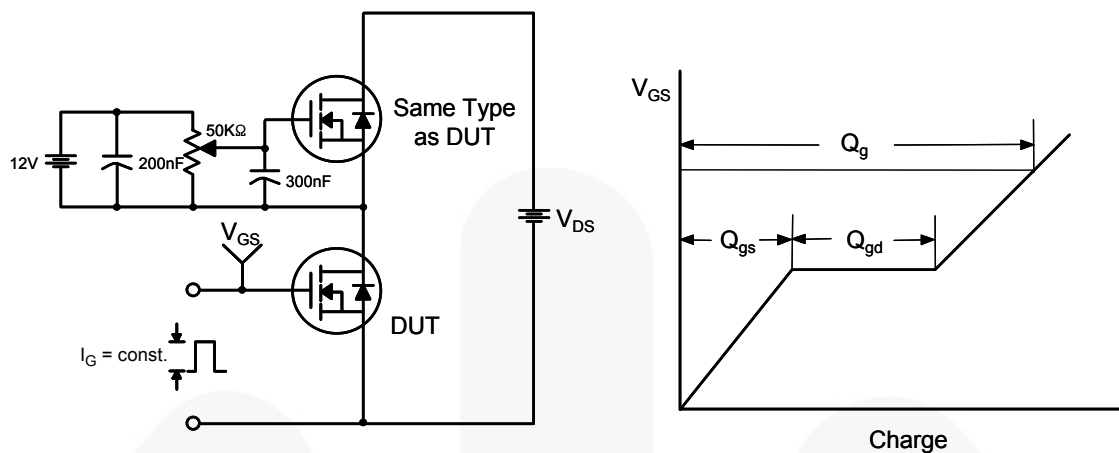


Figure 12. Gate Charge Test Circuit & Waveform

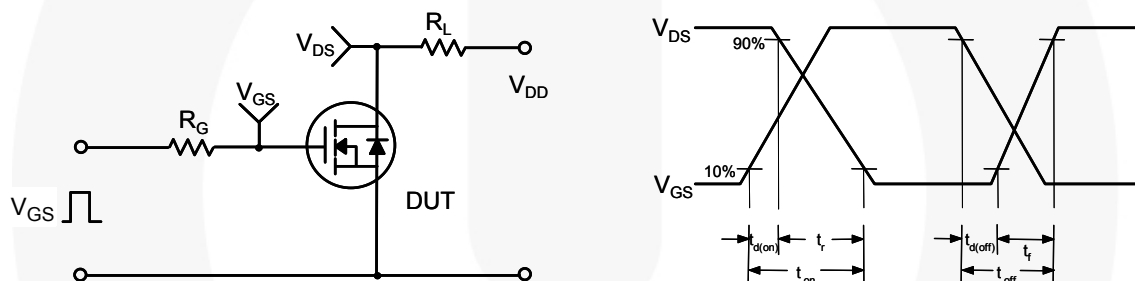


Figure 13. Resistive Switching Test Circuit & Waveforms

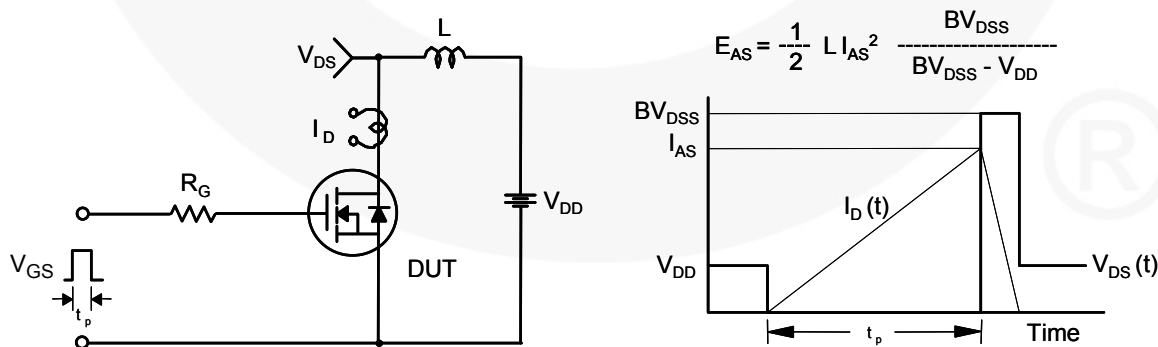
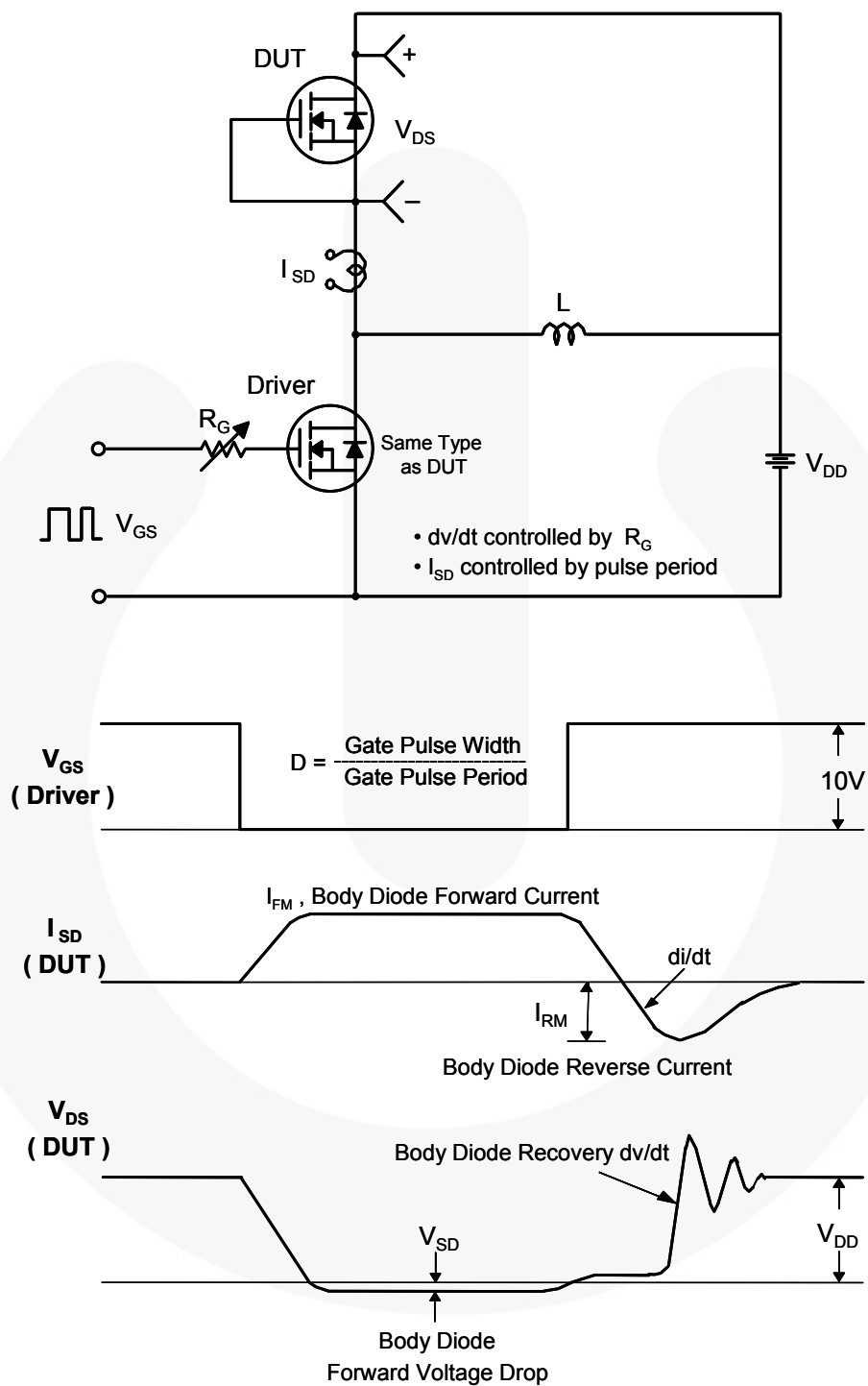
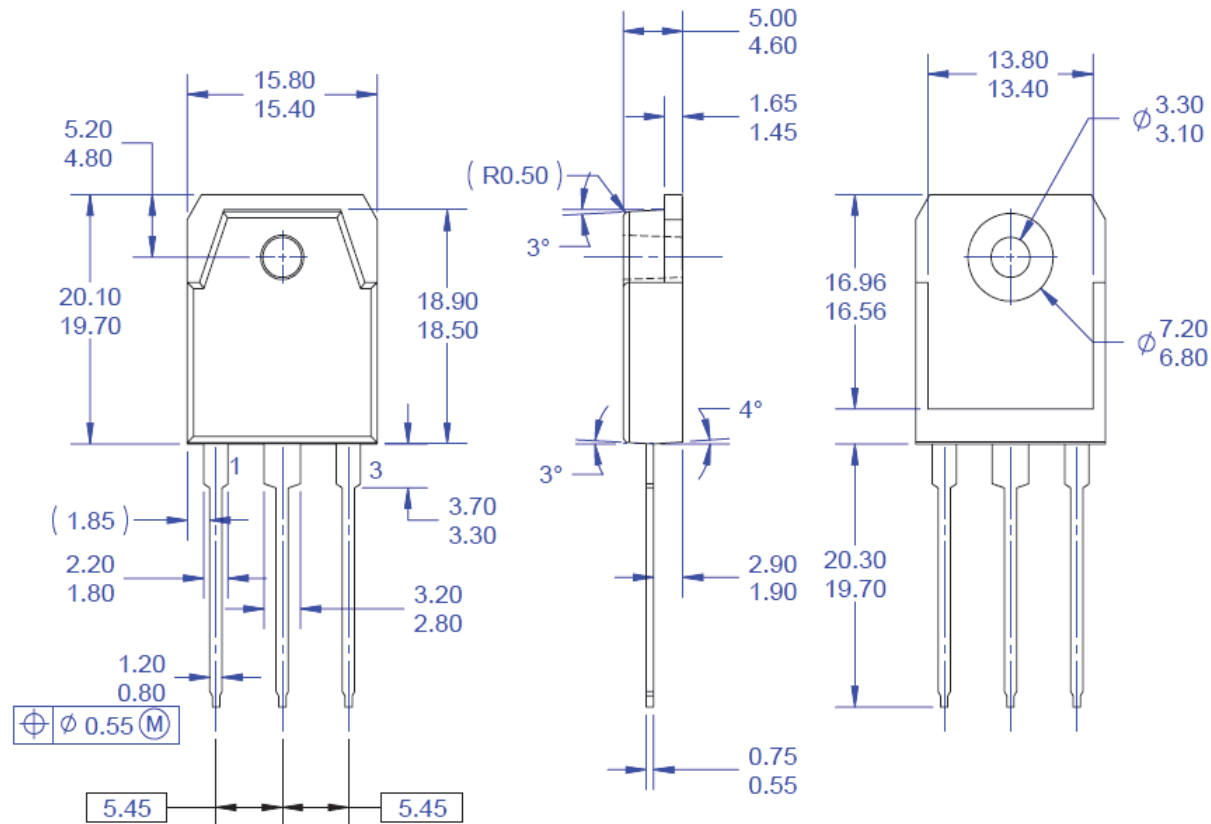


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

## Mechanical Dimensions



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- C) DIMENSION AND TOLERANCING PER ASME14.5
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- F) DRAWING FILE NAME: TO3P03AREV4.

**Figure 16. TO3, 3-Lead, Plastic, EIAJ SC-65**

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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